

## General Description

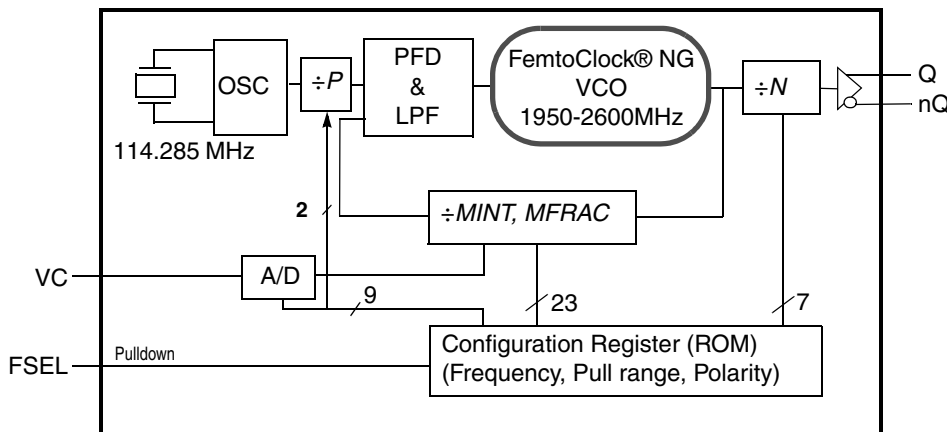
The IDT8N4DV85 is a LVDS Dual-Frequency Programmable VCXO with very flexible frequency and pull-range programming capabilities. The device uses IDT's fourth generation FemtoClock® NG technology for an optimum of high clock frequency and low phase noise performance. The device accepts 2.5V or 3.3V supply and is packaged in a small, lead-free (RoHS 6) 6-lead ceramic 5mm x 7mm x 1.55mm package.

The device can be factory-programmed to any two frequencies in the range of 15.476MHz to 866.67MHz and from 975MHz to 1300 MHz to the very high degree of frequency precision of 218Hz or better. The output frequency is selected by the FSEL pin. The extended temperature range supports wireless infrastructure, telecommunication and networking end equipment requirements.

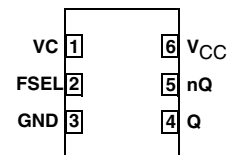
## Features

- Fourth generation FemtoClock® NG technology
- Programmable clock output frequency from 15.476MHz to 866.67MHz and from 975MHz to 1300MHz
- Two factory-programmed output frequencies
- Frequency programming resolution is 218Hz and better
- Absolute pull range (APR) programmable from  $\pm 4.5$  to  $\pm 754.5$ ppm
- One 2.5V or 3.3V LVDS clock output
- Output enable control input, LVCMOS/LVTTL compatible
- RMS phase jitter @ 156.25MHz (12kHz - 20MHz): 0.47ps (typical)
- 2.5V or 3.3V supply voltage
- -40°C to 85°C ambient operating temperature
- Lead-free (RoHS 6) 6-lead ceramic 5mm x 7mm x 1.55mm package

## Block Diagram



## Pin Assignment



**IDT8N4DV85**  
 6-lead ceramic 5mm x 7mm x 1.55mm  
 package body  
 CD Package  
 Top View

## Pin Description and Characteristic Tables

**Table 1. Pin Descriptions**

Number	Name	Type		Description
1	VC	Input		VCXO Control Voltage input.
2	FSEL	Input	Pulldown NOTE 1	Frequency select pin. See Table 3A for function. LVCMOS/LVTTL interface levels.
3	GND	Power		Negative power supply.
4, 5	Q, nQ	Output		Differential clock output. LVDS interface levels.
6	V <sub>CC</sub>	Power		Positive power supply.

NOTE 1. *Pulldown* refers to internal input resistors. See Table 2, *Pin Characteristics*, for typical values

**Table 2. Pin Characteristics**

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
C <sub>IN</sub>	Input Capacitance	FSEL			5.5		pF
		VC			10		pF
R <sub>PULLDOWN</sub>	Input Pulldown Resistor				50		kΩ

## Function Tables

**Table 3A. Output Frequency Range**<sup>NOTE 1</sup>

15.476MHz to 866.67MHz
975MHz to 1300MHz

NOTE 1. Supported output frequency range. The output frequency can be programmed to any frequency in this range and to a precision of 218Hz or better.

## Principles of Operation

The block diagram consists of the internal 3<sup>RD</sup> overtone crystal and oscillator which provide the reference clock  $f_{XTAL}$  of 114.285MHz. The PLL includes the FemtoClock NG VCO along with the Pre-divider ( $P$ ), the feedback divider ( $M$ ) and the post divider ( $N$ ). The  $P$ ,  $M$ , and  $N$  dividers determine the output frequency based on the  $f_{XTAL}$  reference. The feedback divider is fractional supporting a huge number of output frequencies. Internal registers are used to hold up to two different factory pre-set configuration settings. The configuration is selected via the FSEL pin. Changing the FSEL control results in an immediate change of the output frequency to the selected register values. The  $P$ ,  $M$ , and  $N$  frequency configurations support an output frequency range 15.476MHz to 866.67MHz and 975MHz to 1,300MHz.

The devices use the fractional feedback divider with a delta-sigma modulator for noise shaping and robust frequency synthesis capability. The relatively high reference frequency minimizes phase noise generated by frequency multiplication and allows more efficient shaping of noise by the delta-sigma modulator. The output frequency is determined by the 2-bit pre-divider ( $P$ ), the feedback divider ( $M$ ) and the 7-bit post divider ( $N$ ). The feedback divider ( $M$ ) consists of both a 7-bit integer portion ( $MINT$ ) and an 18-bit fractional portion ( $MFRAC$ ) and provides the means for high-resolution frequency generation. The output frequency  $f_{OUT}$  is calculated by:

$$f_{OUT} = f_{XTAL} \cdot \frac{1}{P \cdot N} \cdot \left[ MINT + \frac{MFRAC + 0.5}{2^{18}} \right] \quad (1)$$

**Table 3B. Frequency Selection**

Input	Selects
FSEL	
0 (default)	Frequency 0
1	Frequency 1

## Frequency Configuration

An order code is assigned to each frequency configuration and the VCXO pull-range programmed by the factory (default frequencies). For more information on the available default frequencies and order codes, please see the Ordering Information Section in this document. For available order codes, see the *FemtoClock NG Ceramic-Package XO and VCXO Ordering Product Information* document.

For more information on programming capabilities of the device for custom frequency and pull-range configurations, see the *FemtoClock NG Ceramic 5x7 Module Programming Guide*.

## Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of the product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, $V_{CC}$	3.63V
Inputs, $V_I$	-0.5V to $V_{CC} + 0.5V$
Outputs, $I_O$ (LVDS) Continuous Current Surge Current	10mA 15mA
Package Thermal Impedance, $\theta_{JA}$	49.4°C/W (0 mps)
Storage Temperature, $T_{STG}$	-65°C to 150°C

## DC Electrical Characteristics

**Table 4A. Power Supply DC Characteristics,  $V_{CC} = 3.3V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{CC}$	Power Supply Voltage		3.135	3.3	3.465	V
$I_{DD}$	Power Supply Current			140	175	mA

**Table 4B. Power Supply DC Characteristics,  $V_{CC} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{CC}$	Power Supply Voltage		3.135	3.3	3.465	V
$I_{DD}$	Power Supply Current			136	170	mA

**Table 4C. LVCMOS/LVTTL DC Characteristic,  $V_{CC} = 3.3V \pm 5\%$  or  $V_{CC} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{IH}$	Input High Voltage	$V_{CC} = 3.3V$	2		$V_{CC} + 0.3$	V
		$V_{CC} = 2.5V$	1.7		$V_{CC} + 0.3$	V
$V_{IL}$	Input Low Voltage	$V_{CC} = V_{IN} = 3.465V$	-0.3		0.8	V
		$V_{CC} = V_{IN} = 2.5V$	-0.3		0.7	V
$I_{IH}$	Input High Current	FSEL $V_{CC} = V_{IN} = 3.465V$ or $2.625V$			150	$\mu A$
$I_{IL}$	Input Low Current	FSEL $V_{CC} = 3.465V$ or $2.625V$ , $V_{IN} = 0V$	-5			$\mu A$

**Table 4D. LVDS DC Characteristics,  $V_{CC} = 3.3V \pm 5\%$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{OD}$	Differential Output Voltage		247	330	454	mV
$\Delta V_{OD}$	$V_{OD}$ Magnitude Change				50	mV
$V_{OS}$	Offset Voltage		1.14	1.23	1.31	V
$\Delta V_{OS}$	$V_{OS}$ Magnitude Change				50	mV

**Table 4E. LVDS DC Characteristics,  $V_{CC} = 2.5V \pm 5\%$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{OD}$	Differential Output Voltage		247	320	454	mV
$\Delta V_{OD}$	$V_{OD}$ Magnitude Change				50	mV
$V_{OS}$	Offset Voltage		1.13	1.22	1.30	V
$\Delta V_{OS}$	$V_{OS}$ Magnitude Change				50	mV

## AC Electrical Characteristics

**Table 5A. AC Characteristics,  $V_{CC} = 3.3V \pm 5\%$  or  $V_{CC} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$f_{OUT}$	Output Frequency Q		15.476		866.67	MHz
			975		1300	MHz
$f_I$	Initial Accuracy	Measured @ $25^\circ C$ , $V_C = V_{CC}/2$			$\pm 10$	ppm
$f_S$	Temperature Stability	Option code = A or B			$\pm 100$	ppm
		Option code = E or F			$\pm 50$	ppm
		Option code = K or L			$\pm 20$	ppm
$f_A$	Aging	Frequency drift over 10 year life			$\pm 3$	ppm
		Frequency drift over 15 year life			$\pm 5$	ppm
$f_T$	Total Stability	Option code A, B (10 year life)			$\pm 113$	ppm
		Option code E, F (10 year life)			$\pm 63$	ppm
		Option code K, L (10 year life)			$\pm 33$	ppm
$f_{jit}(cc)$	Cycle-to-Cycle Jitter <sup>NOTE 1</sup>			6	14	ps
$f_{jit}(per)$	RMS Period Jitter <sup>NOTE 1</sup>			4	6	ps
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random) <sup>NOTE 2,3</sup>	156.25MHz, Integration Range: 12kHz - 20MHz		0.47	0.71	ps
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random) <sup>NOTE 2,3</sup> $f_{XTAL} = 114.285MHz$	$15.576MHz \leq f_{out} \leq 100MHz$ , Integration Range: 12kHz - 20MHz		0.76	1.4	ps
		$100MHz < f_{out} \leq 500MHz$ , Integration Range: 12kHz - 20MHz		0.48	0.63	ps
		$500MHz < f_{out} \leq 1300MHz$ , Integration Range: 12kHz - 20MHz		0.46	0.67	ps
$\Phi_N(100)$	Single-side band phase noise, 100Hz from Carrier	156.25MHz		-58		dBc/Hz
$\Phi_N(1k)$	Single-side band phase noise, 1kHz from Carrier	156.25MHz		-86		dBc/Hz
$\Phi_N(10k)$	Single-side band phase noise, 10kHz from Carrier	156.25MHz		-111		dBc/Hz
$\Phi_N(100k)$	Single-side band phase noise, 100kHz from Carrier	156.25MHz		-117		dBc/Hz
$\Phi_N(1M)$	Single-side band phase noise, 1MHz from Carrier	156.25MHz		-126		dBc/Hz
$\Phi_N(10M)$	Single-side band phase noise, 10MHz from Carrier	156.25MHz		-136		dBc/Hz
PSNR	Power Supply Noise Ratio	50mV Sinusoidal Noise 1kHz - 50MHz		-58.7		dBc/Hz
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	80		500	ps

**Table 5A. AC Characteristics,  $V_{CC} = 3.3V \pm 5\%$  or  $V_{CC} = 2.5V \pm 5\%$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
odc	Output Duty Cycle		45		55	%
$t_{OSC}$	Device startup time after power-up				15	ms
$t_{SET}$	Output frequency settling time after FSEL0 and FSEL1 values are changed				1	ms

NOTE 1. This parameter is defined in accordance with JEDEC standard 65.

NOTE 2. Refer to the phase noise plot.

NOTE 3. Refer to the FemtoClock NG Ceramic 5 x 7 Modules Programming Guide for additional information on PLL feedback modes and the optimum configuration for phase noise.

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE: Characterized with  $V_C = V_{CC}/2$ .

NOTE: XTAL parameters (initial accuracy, temperature stability, aging and total stability) are guaranteed by manufacturing.

**Table 5B. VCXO Control Voltage Input ( $V_C$ ) Characteristics,  $V_{CC} = 3.3V \pm 5\%$  or  $V_{CC} = 2.5V \pm 5\%$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$K_V$	Oscillator Gain; NOTE 1, 2, 3	$V_{CC} = 3.3V$	7.57		477.27	ppm/V
	Oscillator Gain NOTE 1, 2, 3	$V_{CC} = 2.5V$	10		630	ppm/V
$L_{VC}$	Control Voltage Linearity	BSL Variation	-1	$\pm 0.1$	+1	%
BW	Modulation Bandwidth			100		kHz
$Z_{VC}$	VC Input Impedance			500		k $\Omega$
$V_{C_{NOM}}$	Nominal Control Voltage			$V_{CC}/2$		V
$V_C$	Control Voltage Tuning Range; NOTE 4		0		$V_{CC}$	V

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500lpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

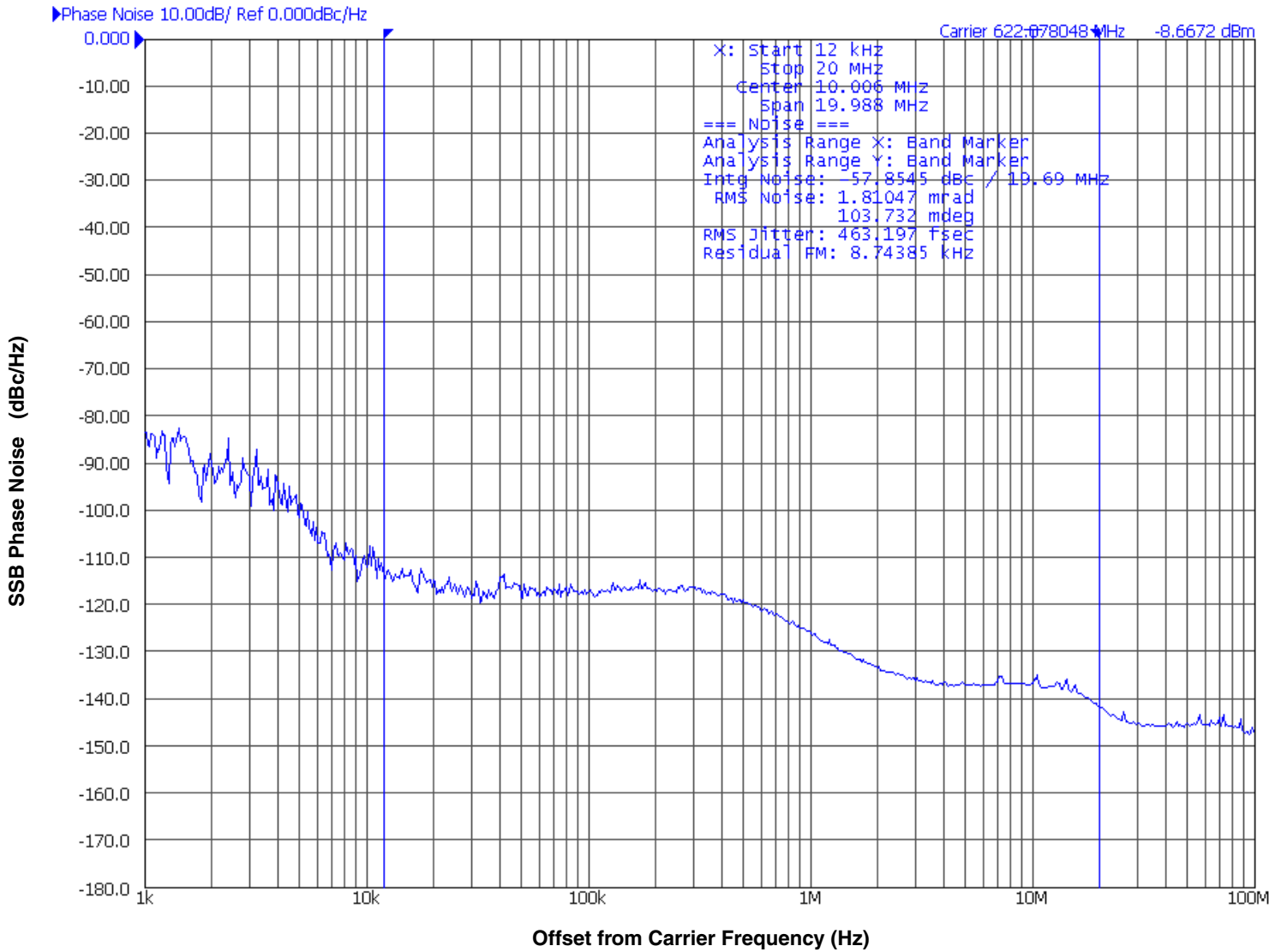
NOTE 1.  $V_C = 0V$  to  $V_{CC}$ . Oscillator gain is programmed by IDT. Gain =  $(25 * N) \div V_{CC}$  and is in the range of  $n = 1$  to  $n = 63$ .

NOTE 2. Nominal oscillator gain: Refer to the programming guide for optimal pull range and control voltage tuning

NOTE 3. For best phase noise performance, use the lowest  $K_V$  that meets the requirements of the application.

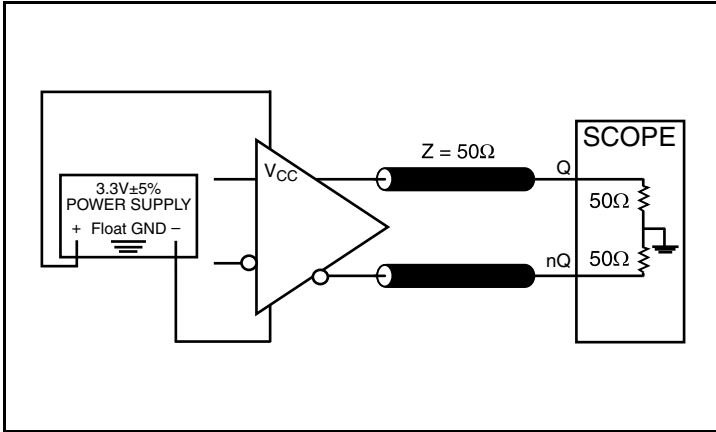
NOTE 4. BSL = Best Straight Line Fit: Variation of the output frequency vs. control voltage  $V_C$  in percent.  $V_C$  ranges from 10% to 90%  $V_{CC}$ .

# RMS Phase Jitter

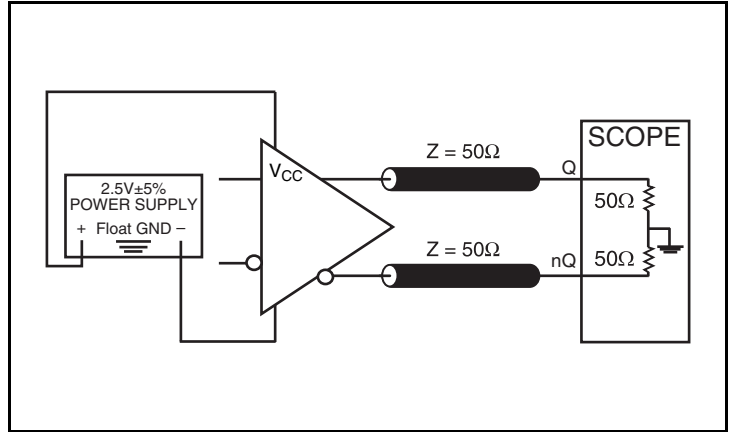




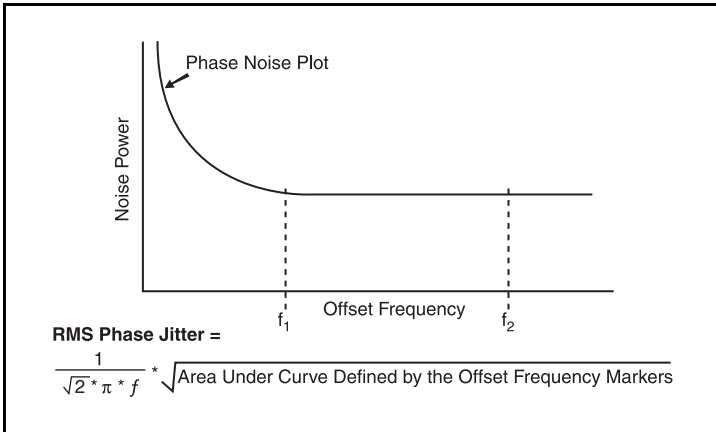
## Parameter Measurement Information



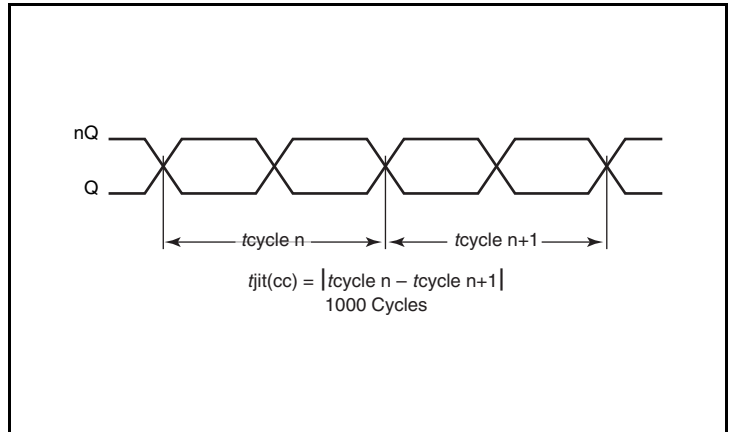
3.3V LVDS Output Load AC Test Circuit



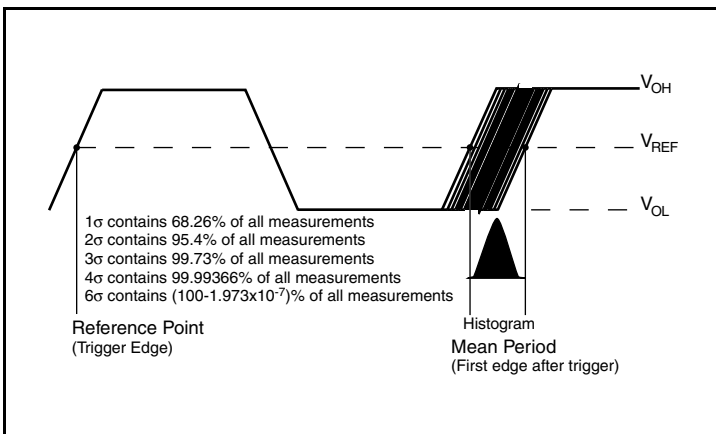
2.5V LVDS Output Load AC Test Circuit



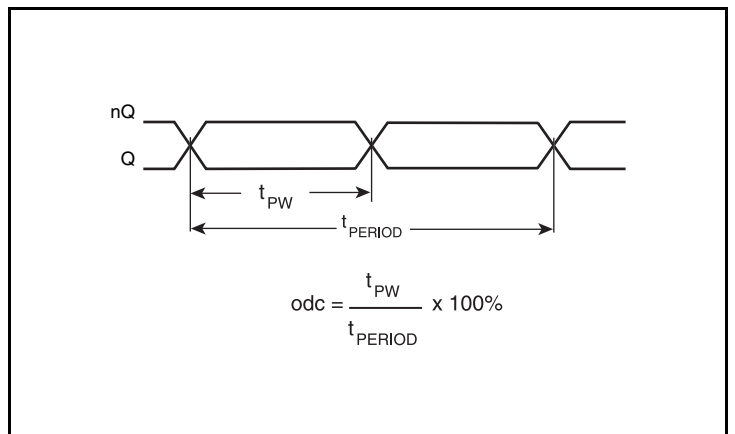
RMS Phase Jitter



Cycle-to-Cycle Jitter

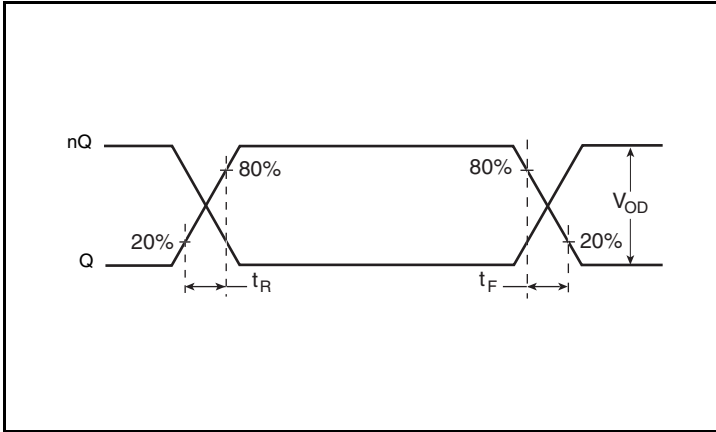


RMS Period Jitter

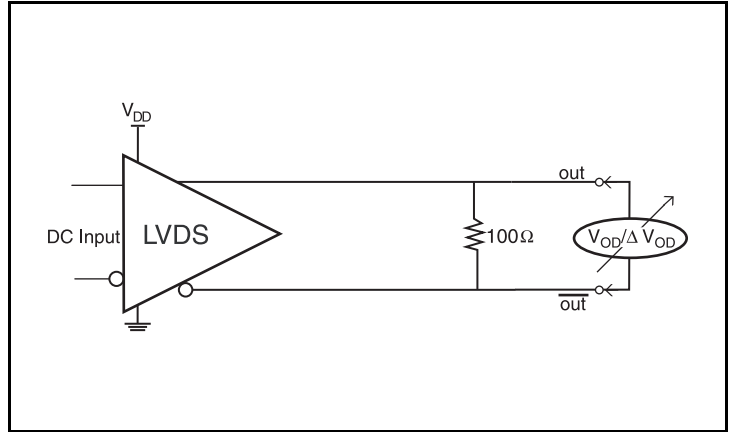


Output Duty Cycle/Pulse Width/Period

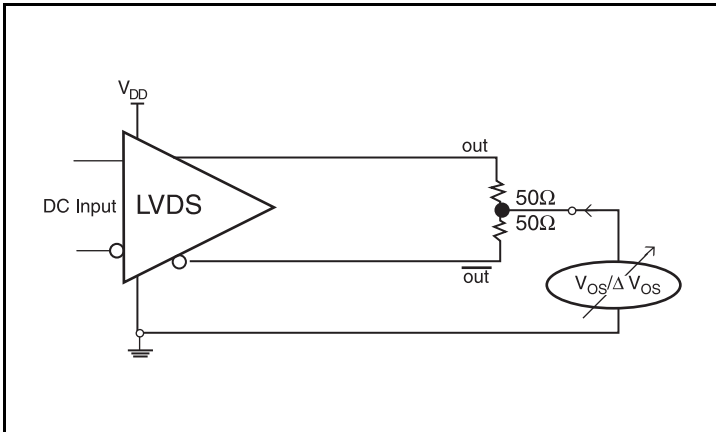
Parameter Measurement Information, continued



Output Rise/Fall Time



Differential Output Voltage Setup



Offset Voltage Setup

## Applications Information

### Recommendations for Unused Input Pins

#### Inputs:

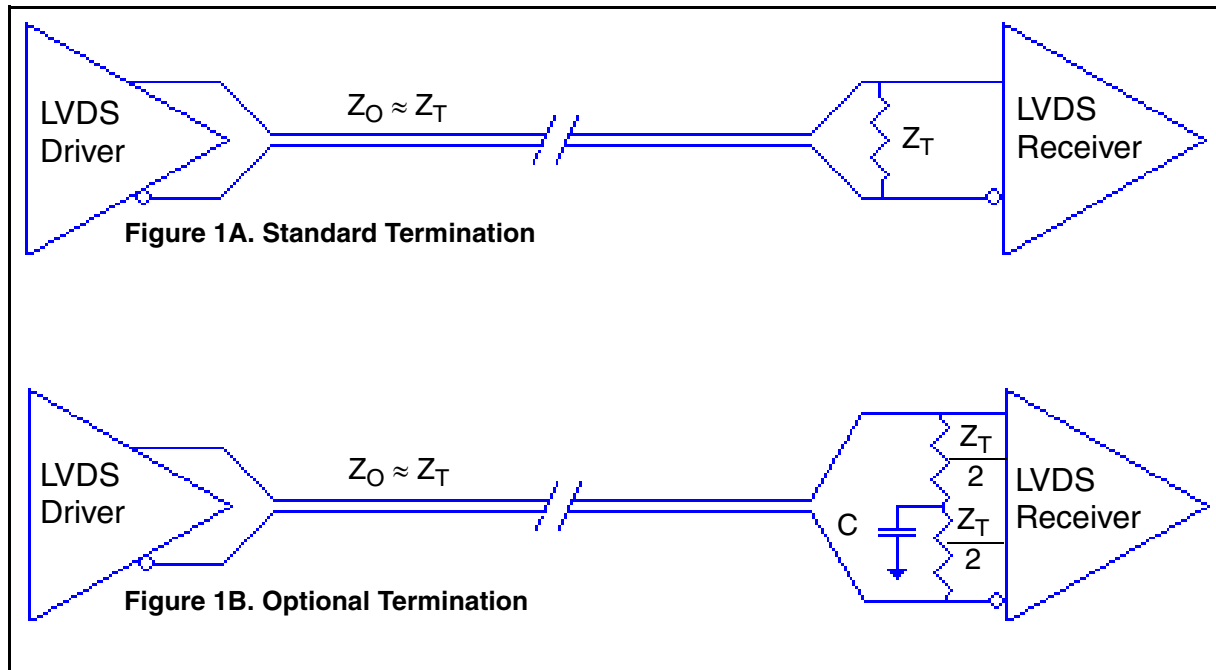
##### LVC MOS Pins

All control pins have internal pulldowns; additional resistance is not required but can be added for additional protection. A 1kΩ resistor can be used.

### LVDS Driver Termination

For a general LVDS interface, the recommended value for the termination impedance ( $Z_T$ ) is between 90Ω and 132Ω. The actual value should be selected to match the differential impedance ( $Z_0$ ) of your transmission line. A typical point-to-point LVDS design uses a 100Ω parallel resistor at the receiver and a 100Ω differential transmission-line environment. In order to avoid any transmission-line reflection issues, the components should be surface mounted and must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The

standard termination schematic as shown in *Figure 1A* can be used with either type of output structure. *Figure 1B*, which can also be used with both output types, is an optional termination with center tap capacitance to help filter common mode noise. The capacitor value should be approximately 50pF. If using a non-standard termination, it is recommended to contact IDT and confirm if the output structure is current source or voltage source type. In addition, since these outputs are LVDS compatible, the input receiver's amplitude and common-mode input range should be verified for compatibility with the output.



## Power Considerations

This section provides information on power dissipation and junction temperature for the IDT8N4DV85. Equations and example calculations are also provided.

### 1. Power Dissipation.

The total power dissipation for the IDT8N4DV85 is the sum of the core power plus the analog power plus the power dissipated in the load(s). The following is the power dissipation for  $V_{CC} = 3.3V + 5\% = 3.465V$ , which gives worst case results.

- Power (core)<sub>MAX</sub> =  $V_{CC\_MAX} * I_{CC\_MAX} = 3.465V * 175mA = 606.375mW$
- 

### 2. Junction Temperature.

Junction temperature,  $T_j$ , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature,  $T_j$ , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for  $T_j$  is as follows:  $T_j = \theta_{JA} * Pd\_total + T_A$

$T_j$  = Junction Temperature

$\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

$Pd\_total$  = Total Device Power Dissipation (example calculation is in section 1 above)

$T_A$  = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming no air flow and a multi-layer board, the appropriate value is 49.4°C/W per Table 6 below.

Therefore,  $T_j$  for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ\text{C} + 0.606\text{W} * 49.4^\circ\text{C/W} = 114.9^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example.  $T_j$  will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

**Table 6. Thermal Resistance  $\theta_{JA}$  for a 6-Lead Ceramic 5mm x 7mm Package, Forced Convection**

$\theta_{JA}$ vs. Air Flow			
Meters per Second	0	1	2
Multi-Layer PCB, JEDEC Standard Test Boards	49.4°C/W	44.2°C/W	42.1°C/W

## Reliability Information

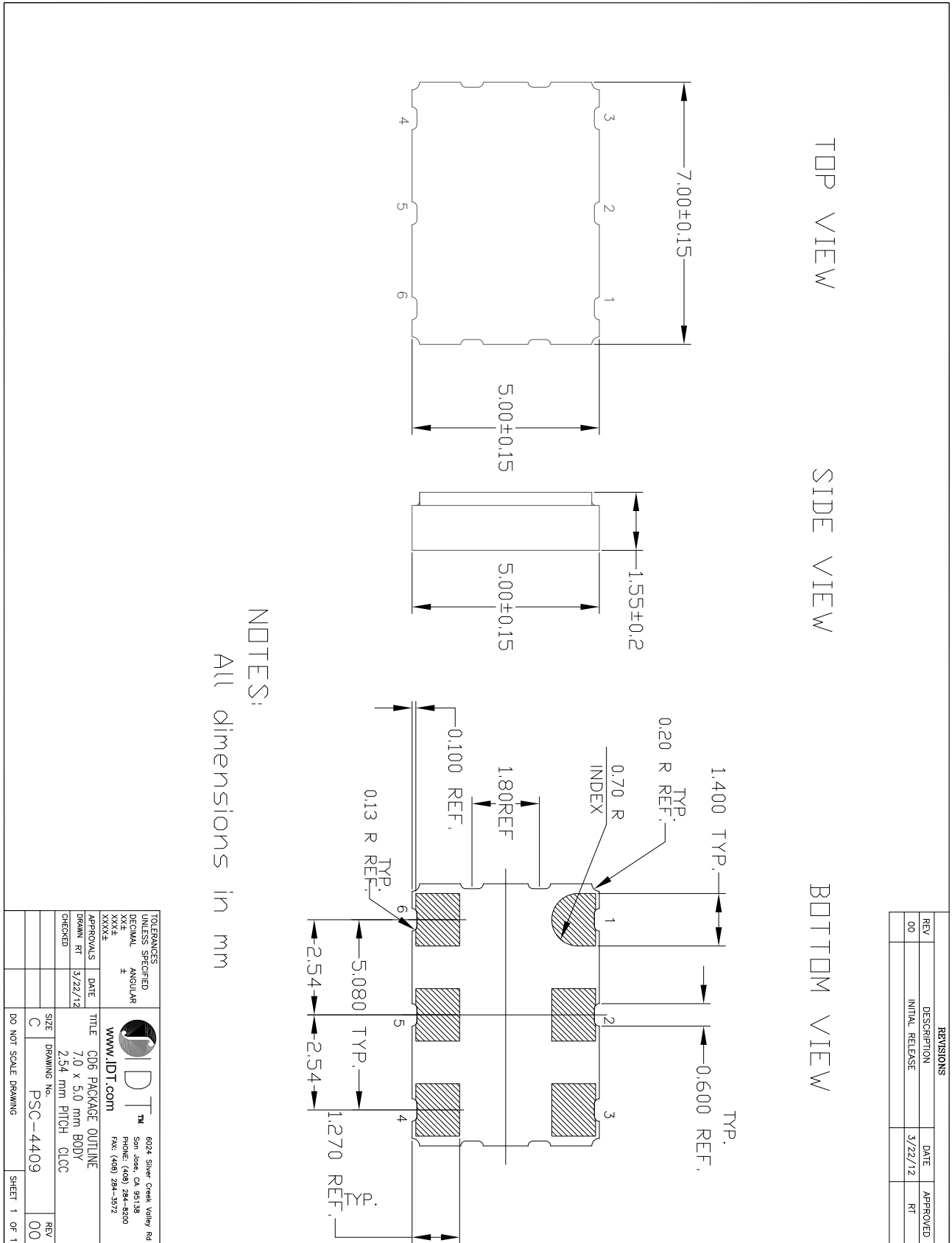
**Table 7.  $\theta_{JA}$  vs. Air Flow Table for a 6-Lead Ceramic 5mm x 7mm Package**

$\theta_{JA}$ vs. Air Flow			
Meters per Second	<b>0</b>	<b>1</b>	<b>2</b>
Multi-Layer PCB, JEDEC Standard Test Boards	49.4°C/W	44.2°C/W	42.1°C/W

## Transistor Count

The transistor count for IDT8N4DV85 is: 47,414

Package Outline and Package Dimensions

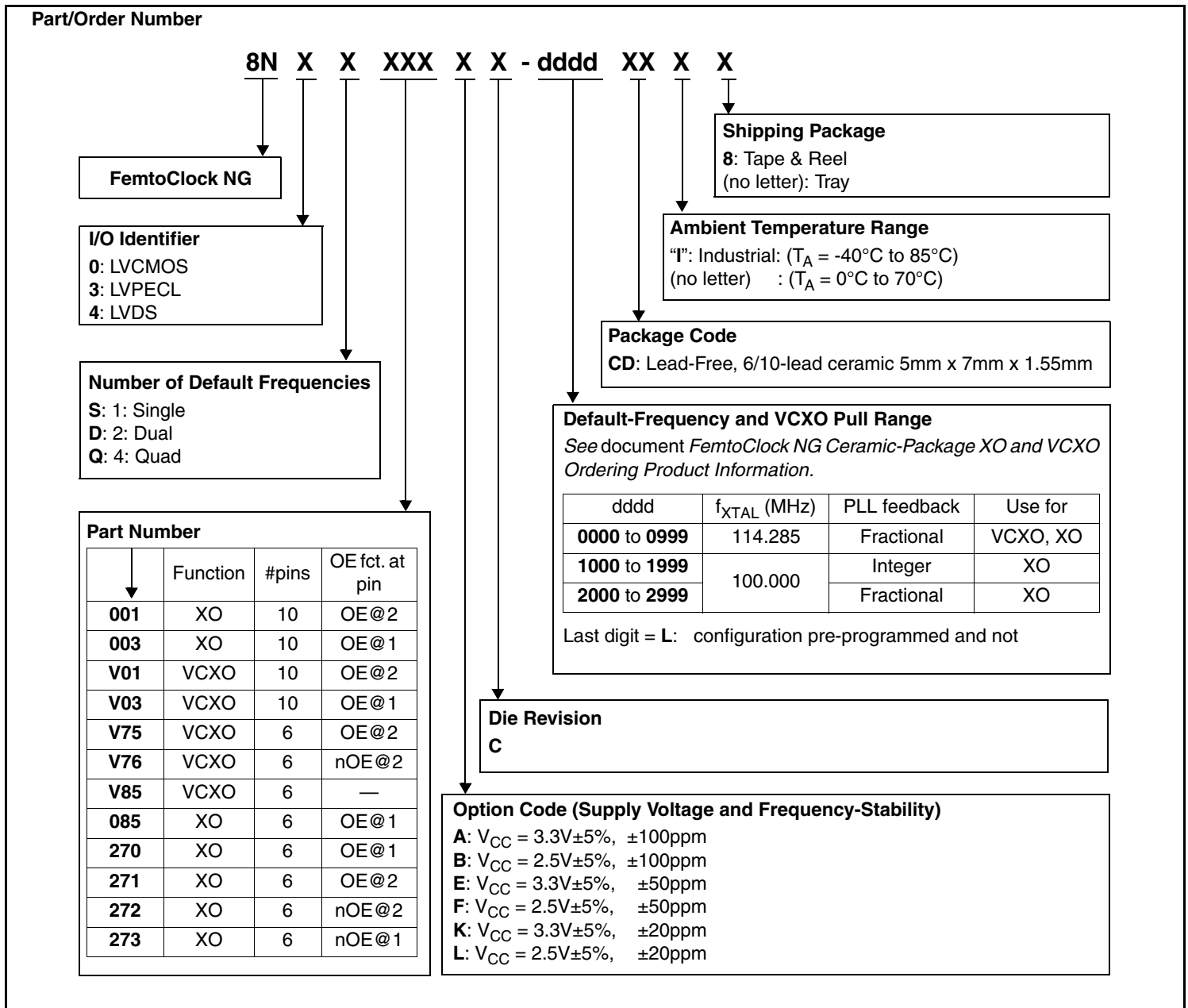


## Ordering Information for FemtoClock NG Ceramic-Package XO and VCXO Products

The programmable VCXO and XO devices support a variety of device options such as the output type, number of default frequencies, internal crystal frequency, power supply voltage, ambient temperature range and the frequency accuracy. The device options, default frequencies and default VCXO pull range must be specified at the time of order and are programmed by IDT before the shipment. The table below specifies the available order codes, including the device options and default frequency configurations. Example part number: the order code 8N3QV01FG-0001CDI specifies a programmable, quad default-frequency VCXO with a voltage supply of 2.5V, a LVPECL output, a  $\pm 50$  ppm crystal frequency accuracy,

contains a 114.285MHz internal crystal as frequency source, industrial temperature range, a lead-free (6/6 RoHS) 6-lead ceramic 5mm x 7mm x 1.55mm package and is factory-programmed to the default frequencies of 100MHz, 122.88MHz, 125MHz and 156.25MHz and to the VCXO pull range of min.  $\pm 100$  ppm.

Other default frequencies and order codes are available from IDT on request. For more information on available default frequencies, see the *FemtoClock NG Ceramic-Package XO and VCXO Ordering Product Information* document.



NOTE: For order information, also see the *FemtoClock NG Ceramic-Package XO and VCXO Ordering Product Information* document.

## Device Marking

Table 8. Device Marking

	Industrial Temperature Range ( $T_A = -40^{\circ}\text{C}$ to $85^{\circ}\text{C}$ )	Commercial Temperature Range ( $T_A = 0^{\circ}\text{C}$ to $70^{\circ}\text{C}$ )
Marking	IDT8N4DV85yC- dddCDI	IDT8N4DV85yC- dddCD
<p><b>x</b> = Number of Default Frequencies, <b>y</b> = Option Code, <b>ddd</b> = Default-Frequency and VCXO Pull Range.</p>		



## Revision History Sheet

Rev	Table	Page	Description of Change	Date
A	T6	4	Absolute Maximum Rating - corrected Package Thermal Impedance.	4/27/12
		12	Power Considerations - corrected Thermal Resistance table, updated Junction Temperature calculation.	
	T7	13	Corrected Air Flow table.	
B	T4D	4	3.3V LVDS DC Characteristics Table - updated specs.	8/22/12
	T4E	5	2.5V LVDS DC Characteristics Table - updated specs. Per PCN #N1206-02.	
B	5A	6	RMS Phase Jitter, Test Conditions, fixed test conditions: 15.576MHz – 100MHz, to $15.576\text{MHz} \leq f_{\text{out}} \leq 100\text{MHz}$ , 100MHz – 500MHz, to $100\text{MHz} < f_{\text{out}} \leq 500\text{MHz}$ , 500MHz – 1300MHz, to $500\text{MHz} < f_{\text{out}} \leq 1300\text{MHz}$	11/20/2013



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(Rev.1.0 Mar 2020)

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